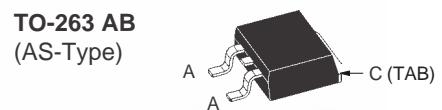
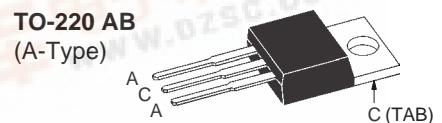
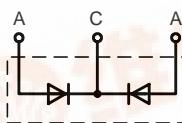




**DSSK 28-01A  
DSSK 28-01AS**

## Power Schottky Rectifier with common cathode

$V_{RSM}$	$V_{RRM}$	Type
V	V	
100	100	DSSK 28-01A
100	100	DSSK 28-01AS



A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		35	A
$I_{FAV}$	$T_c = 155^\circ\text{C}$ ; rectangular, $d = 0.5$	2x15	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sinev	230	A
$E_{AS}$	$I_{AS} = 9.5 \text{ A}$ ; $L = 180 \mu\text{H}$ ; $T_{VJ} = 25^\circ\text{C}$ ; non repetitive	10	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10 \text{ kHz}$ ; repetitive	1	A
$(dv/dt)_{cr}$		5000	$\text{V}/\mu\text{s}$
$T_{VJ}$		-55...+175	$^\circ\text{C}$
$T_{VJM}$		175	$^\circ\text{C}$
$T_{stg}$		-55...+150	$^\circ\text{C}$
$P_{tot}$	$T_c = 25^\circ\text{C}$	105	W
$M_d$	mounting torque (Version A only)	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.5 5	mA mA
$V_F$	$I_F = 15 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$ $I_F = 15 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$ $I_F = 30 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$	0.64 0.79 0.76	V V V
$R_{thJC}$ $R_{thCH}$	(Version A only)	0.5	1.4 K/W K/W

Pulse test: Pulse Width = 5 ms, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

### Features

- International standard package
- Very low  $V_F$
- Extremely low switching losses
- Low IRM-values
- Epoxy meets UL 94V-0

### Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

### Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see IXYS databook 2001

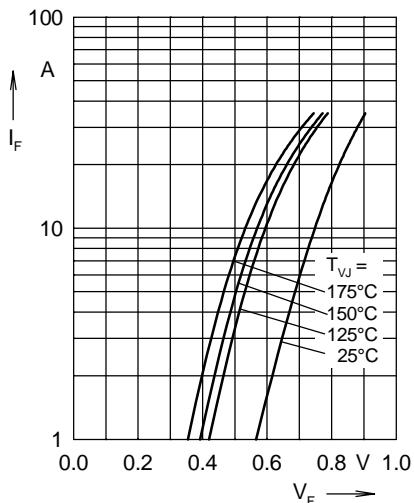


Fig. 1 Maximum forward voltage drop characteristics

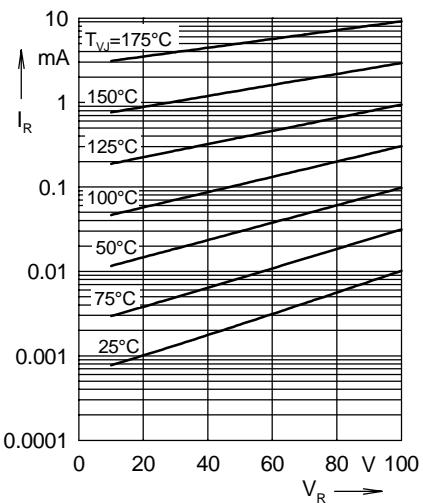


Fig. 2 Typ. value of reverse current  $I_R$  versus reverse voltage  $V_R$

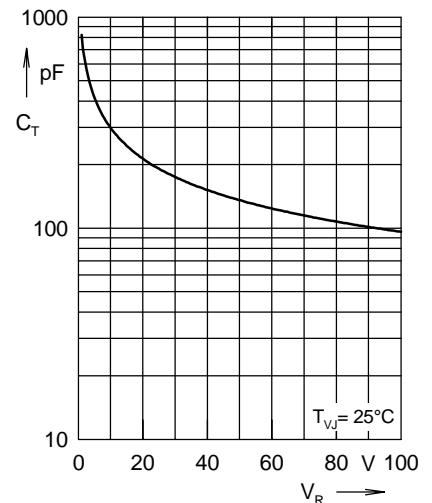


Fig. 3 Typ. junction capacitance  $C_T$  versus reverse voltage  $V_R$

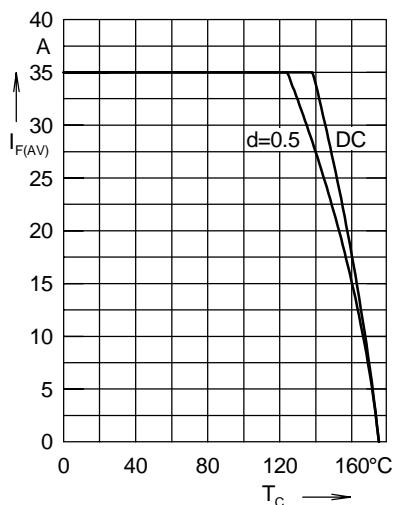


Fig. 4 Average forward current  $I_{F(AV)}$  versus case temperature  $T_C$

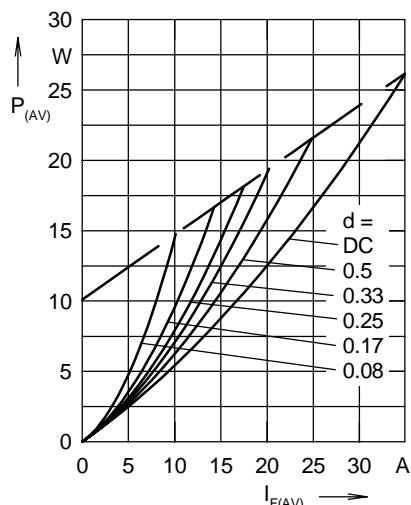


Fig. 5 Forward power loss characteristics

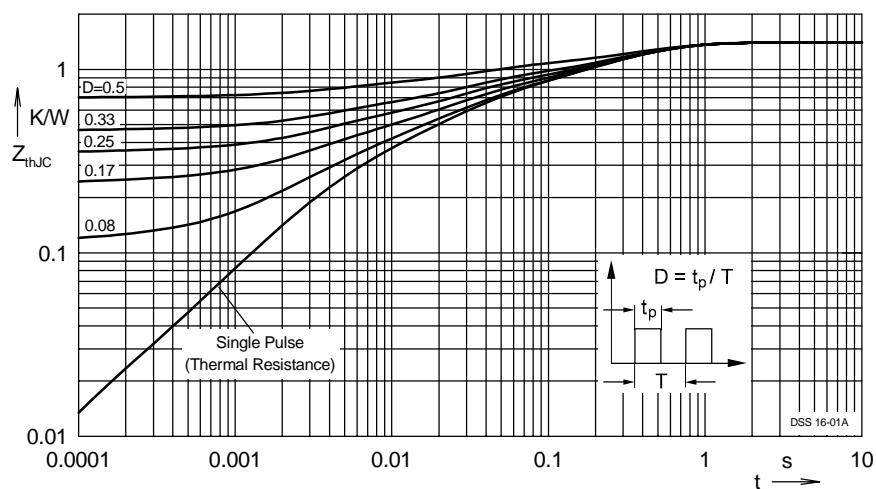


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode